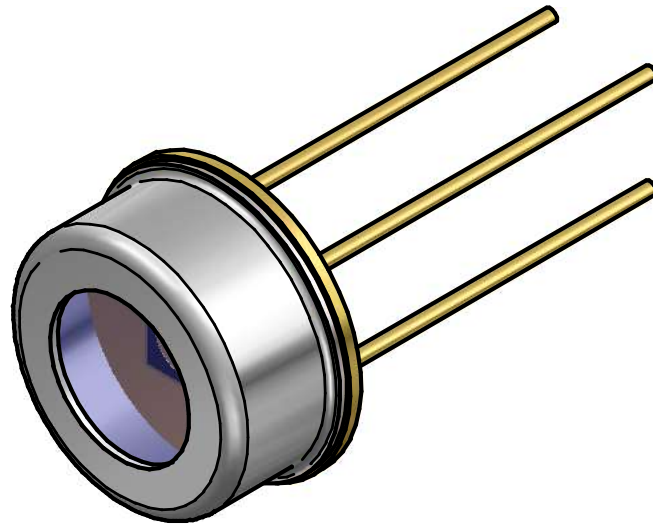


1mm InGaAs PD TO Module
SPECIFICATIONS[Integration]



Contents

General Description	2
Absolute Maximum Ratings	2
Electro-Optical Characteristics	2
Structure	3
Other Requirements	4

General Description

WPPDFDXX series are designed to have various area/diameter and a good linear responsivity up to high power of +15dBm. In addition, it has a high shunt resistance so that users can design low noise receiver using this photodiode.

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{PD}	20	V
Reverse Current	I_R	40	mA
Forward Current	I_F	100	mA
Operating Temperature	T_C	-40 to +85	$^\circ\text{C}$
Storage Temperature	T_{STG}	-40 to +85	$^\circ\text{C}$

Table 1. Absolute Maximum Ratings

Optical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Optical wavelength Range	λ	-	1100	-	1650	nm
Linear range ($\pm 0.2\text{dB}$)			-50		10	dBm

Table 2. Optical Characteristics

Electrical Characteristics (Tc=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Active diameter	D	-		1.0		mm
Dark current	I _D	V _R = 5V			50	nA
Responsivity	R	λ = 1310nm	0.8	0.9		A/W
		λ = 1550nm	0.9	1.0		
Capacitance	C _{PD}	V _R = 5V		50	100	pF
Shunt resistance	R _{SH}	ΔV/ΔI (@0~10mV)		30		MΩ

Table 3. Electro Characteristics

Structure

Dimensional Parameter

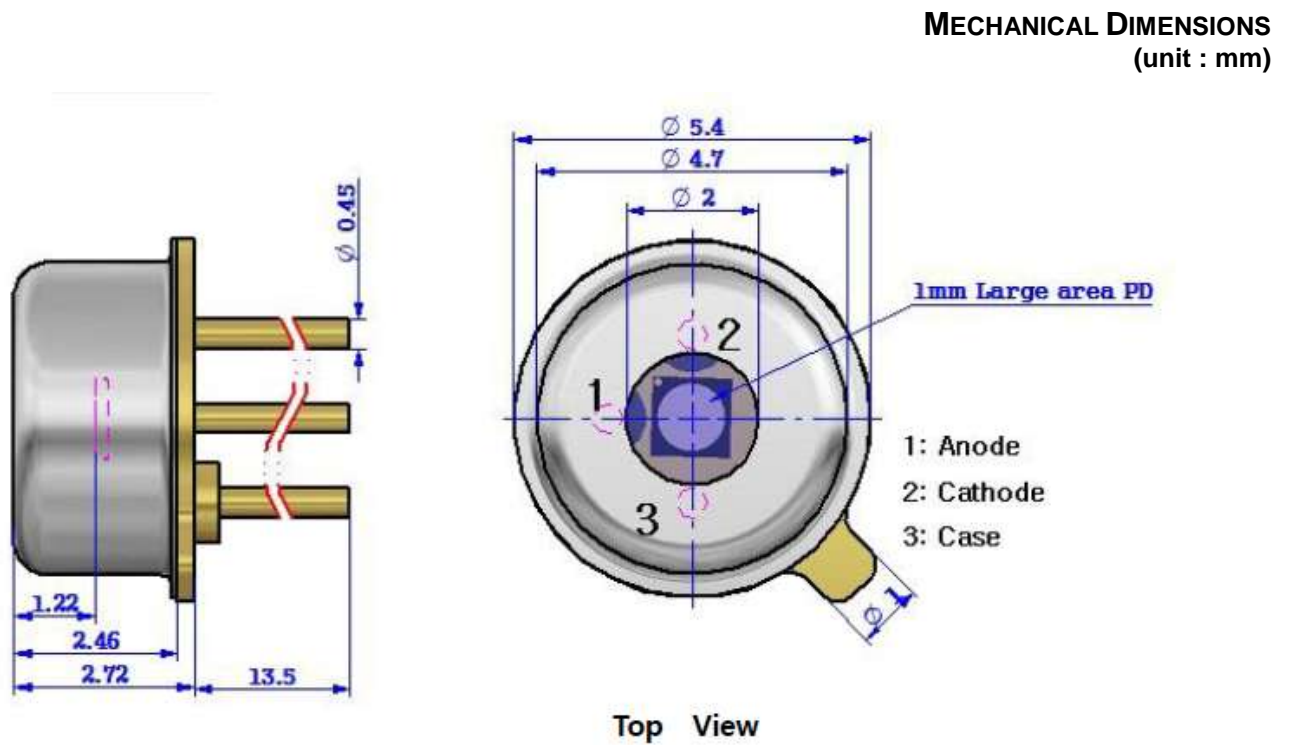


Figure 1. LAPD Dimensional Parameter

Other Requirements

PRECAUTIONS FOR USE

This device is susceptible to damage as a result of ESD(electrostatic discharge). Use of ground straps, anti static mats, and other standard ESD protective equipment is recommended when handling or testing an InGaAs PIN/APD or any other junction photodiode.

Soldering temperature of the leads should not exceed 345°C for more than 3 seconds.

Ordering Information

